Central™
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PCN #: 118
Notification Date:
19 October 2010

Product / Process Change Notice

Parts Affected:
Chip process CP316V, NPN high voltage transistors, wafers, and die in chip form.

Extent of Change:
An overall reduction of the die area.
The CP316V chip process currently measures 20 x 20 mils and is being replaced by the CP336V chip process which measures 17.3 x 17.3 mils.

Reason for Change:
To accommodate assemblies of extremely small surface mount, epoxy molded packages.

Effect of Change:
This change does not affect the electrical characteristics of any device.

Qualification:
Standard evaluation and qualifications completed resulting in no performance differences compared to current product.

Effective Date of Change:
Existing inventory will be shipped until depleted.

Sample Availability:
Please contact Salesperson or Manufacturer's Representative.

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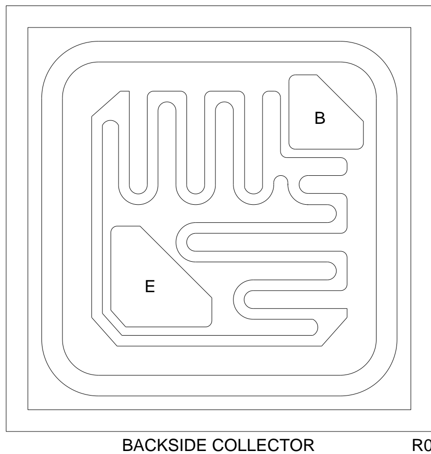
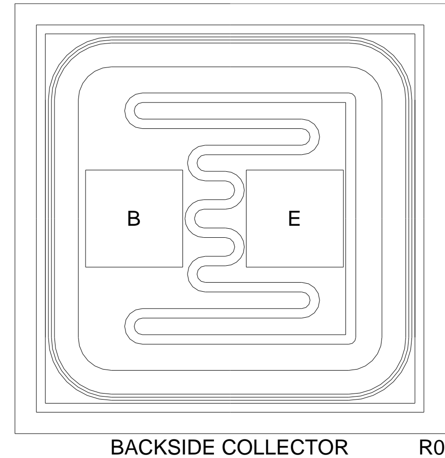
Figures:

Figure 1: CP316V Chip Geometry



Die Size:	20 x 20 mils
Die Thickness:	7.1 mils
Bond Pad Area (Emitter):	4.7 x 4.7 mils
Bond Pad Area (Base):	4 x 4 mils
Topside Metal:	Al (30,000Å)
Backside Metal:	Au (18,000Å)

Figure 2:CP336V Chip Geometry



Die Size:	17.3 x 17.3 mils
Die Thickness:	7.1 mils
Bond Pad Area (Emitter):	3.9 x 3.9 mils
Bond Pad Area (Base):	3.9 x 3.9 mils
Topside Metal:	Al (30,000Å)
Backside Metal:	Au (12,000Å)

Part Numbers Affected:

CP316V-2N5551-CTAN
CP316V-2N5551-CT
CP316V-2N5551-WN
CMLT5551
CMLT5554
CMPT5551
CMPT5551E
CMUT5551
CMUT5551E
CXT5551
CXT5551E
CZT5551
CZT5551E
2N5551
2N5832